Unit in mm

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

TLP181

Office Machine
Programmable Controllers
AC / DC-Input Module
Telecommunication

The TOSHIBA mini flat coupler TLP181 is a small outline coupler, suitable for surface mount assembly.

TLP181 consist of a photo transistor optically coupled to a gallium arsenide infrared emitting diode.

- Collector-emitter voltage: 80V (min.)
- Current transfer ratio: 50% (min.)

Rank GB: 100% (min.)

- Isolation voltage: 3750Vrms (min.)
- UL recognized: UL1577,

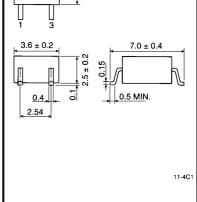
file no. E67349

• Option (V4) type

VDE approved: VDE0884 satisfied

Maximum operating insulation voltage: 565VPK

Highest permissible over voltage: 6000VPK

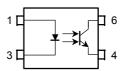


11-4C1

Weight: 0.09 g

TOSHIBA

Pin Configuration (top view)



- 1: Anode
- 3: Cathode
- 4: Emitter
- 6: Collector

Current Transfer Ratio

			sfer Ratio (%) / I _F)			
Туре	Classification *1	I _F = 5mA, V _{CE}	= 5V, Ta = 25°C	Marking Of Classification		
		Min.	Max.			
	(None)	50	600	BLANK, Y, Y, G, G, B, B, GB		
	Rank Y	50	150	Y, Y**		
TLP181	Rank GR	100	300	G, G "		
	Rank BL	200	600	B, B*		
	Rank GB	100	600	G, G [■] , B, B [■] , GB		

^{*1:} EX, Rank GB: TLP181 (GB)

⁽Note) Application, type name for certification test, please use standard product type name, i, e. TLP181 (GB): TLP181

Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit
	Forward current	lF	50	mA
	Forward current detating	ΔI _F / °C	–0.7 (Ta ≥ 53°C)	mA / °C
LED	Pulse forward current (100µs pulse, 100pps)	I _{FP}	1	А
	Reverse voltage	V _R	5	V
	Junction temperature	Tj	125	°C
	Collector-emitter voltage	V _{CEO}	80	V
	Emitter-collector valtage	V _{ECO}	7	V
5	Collector current	IC	50	mA
Detecto	Collector power dissipation (1 Circuit)	PC	150	mW
	Collector power dissipation derating (1 Circuit Ta ≥ 25°C)	ΔP _C / °C	-1.5	mW / °C
	Junction temperature	Tj	125	°C
Sto	rage temperature range	T _{stg}	−55 ~ 125	°C
Оре	erating temperature range	T _{opr}	−55 ~ 100	°C
Lea	d soldering temperature	T _{sol}	260 (10s)	°C
Total package power dissipation		P _T	200	mW
Total package power dissipation derating (Ta ≥ 25°C)		ΔP _T / °C	-2.0	mW / °C
Isolation voltage (AC, 1min., R.H. ≤ 60%) (Note 1)		BVS	3750	V _{rms}

(Note 1) Device considered a two-terminal device: Pin1, 3 shorted together and pins 4, 6 shorted together

Recommended Operating Conditions

Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{CC}	_	5	48	V
Forward current	lF	_	16	20	mA
Collector current	IC	_	1	10	mA
Operating temperature	T _{opr}	-25	_	85	°C

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
	Forward voltage	V _F	I _F = 10 mA	1.0	1.15	1.3	V
E	Reverse current	I _R	V _R = 5 V	_	_	10	μA
	Capacitance	C _T	V = 0, f = 1 MHz	_	30	_	pF
	Collector–emitter breakdown voltage	V _(BR) CEO	I _C = 0.5 mA	80	_	_	V
5	Emitter-collector breakdown voltage	V _{(BR) ECO}	I _E = 0.1 mA	7	_	_	V
Detector	Collector dark current I _{CEO}	loro	V _{CE} = 48 V, (Ambient light below 1000 lx)	_	0.01 (2)	0.1 (10)	μΑ
		V _{CE} = 48 V, Ta = 85°C, (Ambient light below 1000 lx)		2 (4)	50 (50)	μΑ	
	Capacitance (collector to emitter)	C _{CE}	V = 0, f = 1 MHz	_	10	_	pF

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	MIn.	Тур.	Max.	Unit
Current transfer ratio	I _C / I _E	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ Rank GB	50		600	%
Current transfer fatto	1C / IF		100	_	600	
Saturated CTR	I _C / I _{F (sat)}	IF = 1 mA, V _{CE} = 0.4 V Rank GB	-	60	_	- %
Saturated CTIV			30	_	_	
	VCE (sat)	I _C = 2.4 mA, I _F = 8 mA		_	0.4	
Collector-emitter saturation voltage		I _C = 0.2 mA, I _F = 1 mA Rank GB		0.2	_	V
3				_	0.4	
Off-state collector current	I _{C (off)}	V _F = 0.7V, V _{CE} = 48 V	_	1	10	μΑ

Isolation Characteristics (Ta = 25°C)

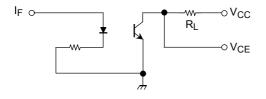
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Capacitance (input to output)	C _S	V _S = 0V, f = 1 MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500 V, R.H. ≤ 60%	1×10 ¹²	10 ¹⁴	_	Ω
		AC, 1 minute	3750	-	_	V
Isolation voltage	BV_S	AC, 1 second, in oil	_	10000	_	V _{rms}
		DC, 1 minute, in oil	_	10000		V _{dc}

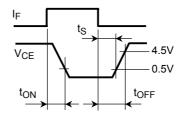
4

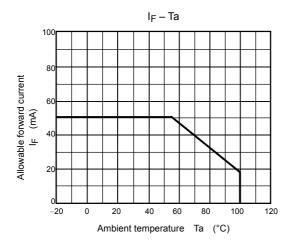
Swiching Characteristics (Ta = 25°C)

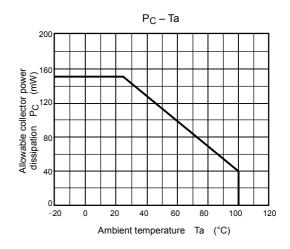
Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Rise time	t _r		_	2	_	
Fall time	t _f	V _{CC} = 10 V, I _C = 2 mA	_	3	_	μs
Turn-on time	t _{on}	$R_L = 100\Omega$	_	3	_	
Turn-off time	t _{off}		_	3	_	
Turn-on time	t _{ON}		_	2	_	
Storage time	ts	$R_L = 1.9 \text{ k}\Omega$ (Fig.1) $V_{CC} = 5 \text{ V}, I_F = 16 \text{ mA}$	_	25	_	μs
Turn-off time	t _{OFF}		_	40	_	

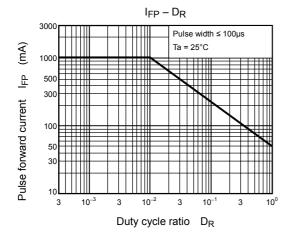
Fig. 1 Switching time test circuit

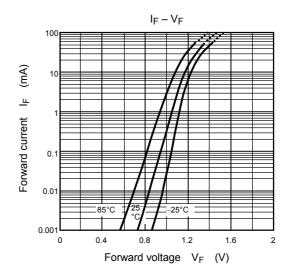


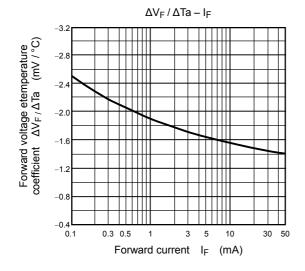


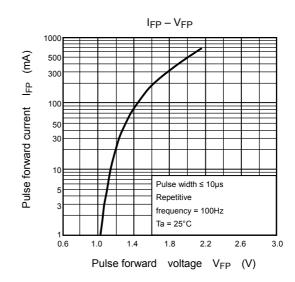


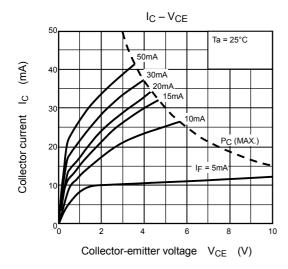


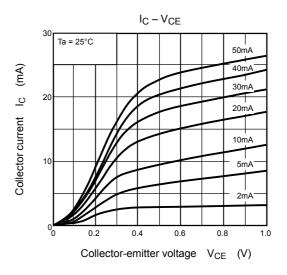


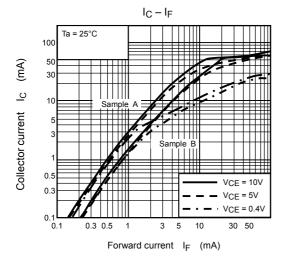


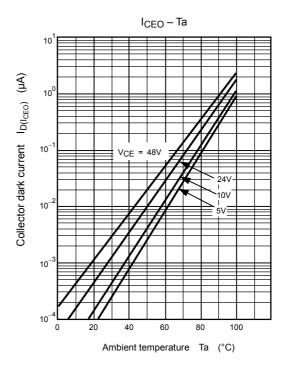


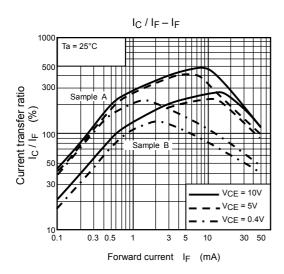


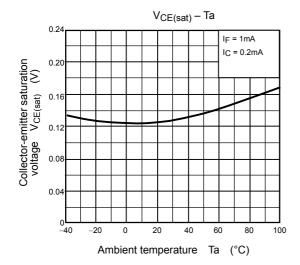


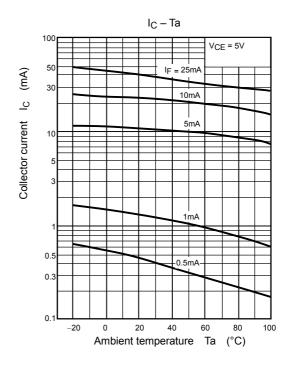


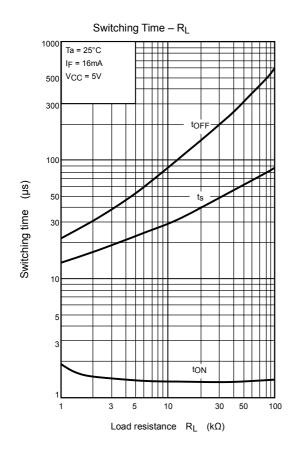


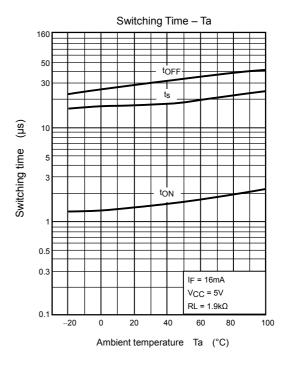












RESTRICTIONS ON PRODUCT USE

000707EBC

- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..
- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- Gallium arsenide (GaAs) is a substance used in the products described in this document. GaAs dust and fumes
 are toxic. Do not break, cut or pulverize the product, or use chemicals to dissolve them. When disposing of the
 products, follow the appropriate regulations. Do not dispose of the products with other industrial waste or with
 domestic garbage.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- The information contained herein is presented only as a guide for the applications of our products. No
 responsibility is assumed by TOSHIBA CORPORATION for any infringements of intellectual property or other
 rights of the third parties which may result from its use. No license is granted by implication or otherwise under
 any intellectual property or other rights of TOSHIBA CORPORATION or others.
- The information contained herein is subject to change without notice.

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.